

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

RECEIVED

Kuniaki YAGI, et al.

JUN 0 5 2002

Appln. No.: 10/050,570

Group Art Unit: 1765

TC 1700

Confirmation No.: 7078

Examiner: Not Yet Assigned

Filed: January 18, 2002

For:

SINGLE CRYSTAL SIC AND METHOD OF PRODUCING THE SAME AS WELL AS SIC

SEMICONDUCTOR DEVICE AND SIC COMPOSITE MATERIAL

REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

Commissioner for Patents Office of Initial Patent Examination Customer Service Center Washington, D.C. 20231

Sir:

We enclose a copy of the Official Filing Receipt for the above-identified application and request the following correction(s):

Title: Please change: "Single crystal SiCand method of producing the same as well as SiC semiconductor device and SiC composite material" to -- Single crystal <u>SiC and</u> method of producing the same as well as SiC semiconductor device and SiC composite material--.

Verification for the requested correction(s) is indicated on the original Declaration and Power of Attorney filed January 18, 2002.

Respectfully submitted,

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Date: May 24, 2002

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 APPLICATION NUMBER
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 ATTY.DOCKET.NO
 DRAWINGS
 TOT CLAIMS
 IND CLAIMS

 10/050.570
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CONFIRMATION NO. 7078

23373 SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. WASHINGTON, DC 20037 FILING RECEIPT

OC000000007697631

Date Mailed: 03/22/2002

Receipt is acknowledged of this nonprovisional Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Customer Service Center. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Kuniaki Yagi, Oume-shi, JAPAN; V Hiroyuki Nagasawa, Hachiouji-shi, JAPAN;

Assignment For Published Patent Application HOYA CORPORATION;

Domestic Priority data as claimed by applicant

Foreign Applications

JAPAN 11312/2001 01/19/2001

If Required, Foreign Filing License Granted 03/21/2002

Projected Publication Date: 07/25/2002

Non-Publication Request: No

Early Publication Request: No

Title

Single crystal SiCand method of producing the same as well as SiC semiconductor device and SiC composite material

-- Single crystal SIC and method of producing the same as well as SiC semi conductor derive and SiC composite material --

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9-1820 湘雪望着

DECLARATION AND POWER OF ATTORNEY FOR UTILITY OR DESIGN PATENT APPLICATION (37 CFR 1.63)

As a below named inventor, I hereby declare that: My residence, mailing address, and citizenship are as stated below next to my name. I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

SINGLE CRYSTAL SIC AND METHO	OF PROD	UCING THE S	AME AS WELL AS	Sic SEMI	CONDUCTO	R DEVICE
AND SiC COMPOSITE MATERIAL						
the application of which 図 is attached hereto	OR	Number o	ed on r PCT International A tion No	Application Nu	mber amended o	
I hereby state that I have reviewed and un by any amendment specifically referred to		contents of the	above identified appl	ication, includ	ing the clain	ns, as amended
I acknowledge the duty to disclose info continuation-in-part application(s), materia the national or PCT international filing dat	al informatio	n which became	available between t			
I hereby claim foreign priority benefits un or plant breeder's rights certificate(s), or 3 than the United States of America, listed patent, inventor's or plant breeder's rights application on which priority is claimed.	365(a) of any below and h	PCT internation ave also identified	nal application(s) whed below, by checki	nich designated ng the box, an	d at least on y foreign ap iling date b	ne country other oplication(s) for efore that of the
Prior Foreign Application Number(s)	Co	untry	Foreign Filing Da	ite	Priority (Yes	Claimed No
11312/2001	Ja	pan	Jan. 19, 20	01		
I hereby claim domestic priority benefits a States provisional application(s), or §365 insofar as the subject matter of each of International application in the manner pro- to disclose any information material to the	(c) of any PC f the claims ovided by the e patentabilit	T International of this applicate first paragraph by of this applicate.	application(s) design ion is not disclosed of Title 35, United S ition as defined in 3'	nating the Unit in a listed p States Code, §1 7 C.F.R. 1.56	ed States, li rior United 112, I ackno	sted below and States or PC wledge my dut
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filing date of the prior application and the Prior U.S. or International Application Num			rnational Filing Date		Stat	us

d discretion of Sughrue Mion, PLLC, and request that all correspondence about the application be addressed to the address filed under the same USPTO Customer Number.



PATENT TRADEMARK OFFICE

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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Inventor's Signature						Date			
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Mailing Address:	Γ								
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City	State		Zip				Country		
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Inventor's Signature						Date			
Residence: City	State		Country				Citizenship		
Mailing Address:						•			
B									